.M6165/LM6265/LM6365 High Speed Operational Amplifier

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September 1995

300 V/µs

80 ns to 0.1%

4.75V to 32V

725 MHz

5 mA

< 0.1%

<0.1°

National Semiconductor

LM6165/LM6265/LM6365 High Speed Operational Amplifier

General Description

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The LM6165 family of high-speed amplifiers exhibits an excellent speed-power product in delivering 300 V/ μ s and 725 MHz GBW (stable for gains as low as +25) with only 5 mA of supply current. Further power savings and application convenience are possible by taking advantage of the wide dynamic range in operating supply voltage which extends all the way down to +5V.

These amplifiers are built with National's VIPTM (Vertically Integrated PNP) process which produces fast PNP transistors that are true complements to the already fast NPN devices. This advanced junction-isolated process delivers high speed performance without the need for complex and expensive dielectric isolation.

Features

- High slew rate
- High GBW product
- Low supply current
- Fast settling
- Low differential gain
 Low differential phase
 - Low differential phaseWide supply range
- Stable with unlimited capacitive load
- Applications

Video amplifier

- Wide-bandwidth signal conditioning
- Radar
- Sonar

Connection Diagrams

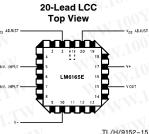
	Lead Flatp Top View	ak
NC 1 V ₀₅ ADJUST 2 INV INPUT 4 NON-INV INPUT 4 V- 5	• LM6165W	10 NC 9 V _{OS} ADJUST 8 V+ 7 V _{OUTPUT} 6 NC

TL/H/9152-14 Order Number LM6165W/883 See NS Package Number W10A

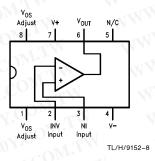
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TL/H/9152



Order Number LM6165E/883 See NS Package Number E20A



Order Number LM6165J/883 See NS Package Number J08A

Order Number LM6365M See NS Package Number M08A

- Order Number LM6265N or
- LM6365N See NS Package Number N08E

$\begin{array}{l} \mbox{Military} \\ -55^{\circ}\mbox{C} \leq \mbox{T}_{\mbox{A}} \leq \ + \ 125^{\circ}\mbox{C} \end{array}$	Industrial $-25^{\circ}C \leq T_{A} \leq +85^{\circ}C$	$\begin{array}{l} \mbox{Commercial} \\ 0^{\circ}\mbox{C} \leq \mbox{T}_{\mbox{A}} \leq \ + \ 70^{\circ}\mbox{C} \end{array}$	Package	NSC Drawing	
	LM6265N	LM6365N	8-Pin Molded DIP	N08E	
LM6165J/883 5962-8962501PA	WW.IC	COM	8-Pin Ceramic DIP	J08A	
	WW.	LM6365M	8-Pin Molded Surface Mt.	M08A	
LM6165E/883 5962-89625012A	WW	.100 1. CO	20-Lead LCC	E20A	
LM6165W883 5962-8962501HA		N.1001.	10-Pin Ceramic Flatpak	W10A	

RRD-B30M115/Printed in U. S. A.

RRD-B30M11

150°C

±700V

WWW.100Y.COM.TW Absolute Maximum Ratings

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If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications. Supply Voltage ($V^+ - V^-$) 36V

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	ounting Methods and Their Effect r other methods of soldering sur-
Storage Temp Range	-65°C to +150°C

Differential Input Voltage (Note	6) ±8V
Common-Mode Voltage Range (Note 10)	e (V ⁺ - 0.7V) to (V ⁻ + 0.7V)
Output Short Circuit to GND (N	ote 1) Continuous
Soldering Information Dual-In-Line Package (N, J) Soldering (10 sec.)	260°C
Small Outline Package (M) Vapor Phase (60 sec.)	215°C
Infrared (15 sec.)	220°C

ESD Tolerance (Notes 6 and 7) **Operating Ratings**

Max Junction Temperature (Note 2)

Temperature Range (Note 2)	
LM6165, LM6165J/883	$-55^{\circ}C \le T_{J} \le +125^{\circ}C$
LM6265	$-25^{\circ}C \le T_{J} \le +85^{\circ}C$
LM6365	$0^{\circ}C \le T_{J} \le +70^{\circ}C$
Supply Voltage Range	4.75V to 32V

DC Electrical Characteristics

. The		Wre Is	N.10	LM6165	LM6265	LM6365	5	
Symbol	Parameter	Conditions	Тур	Limit (Notes 3, 11)	Limit (Note 3)	Limit (Note 3)	Units	
Vos	Input Offset Voltage	W WI	WY.Y	3 4	3 4	6 7	mV Max	
Vos Drift	Input Offset Voltage Average Drift	M.TW Y	3	100Y.CUT	M.TW		μV/°C	
I _b	Input Bias Current	OM.TW	2.5	3 6	3 5	5 6	μA Max	
los	Input Offset Current	COM.TV	150	350 800	350 600	1500 1900	nA Max	
l _{OS} Drift	Input Offset Current Average Drift	L.COM.TW	0.3	NN.100Y	COM	LM.	nA/°C	
R _{IN}	Input Resistance	Differential	20 🔨	NNN.	I.COM	WT	kΩ	
C _{IN}	Input Capacitance	COM	6.0	WWW.Loc	J CON	L	pF	
VOL	Large Signal Voltage Gain	$V_{OUT} = \pm 10V,$ $R_{L} = 2 k\Omega$	10.5	7.5 5.0	7.5 6.0	5.5 5.0	V/mV Min	
	(Note 9)	$R_L = 10 k\Omega$	38	· WWW		DVr.	IVIIII	
СМ	Input Common-Mode Voltage Range		+ 14.0	+ 13.9 + 13.8	+ 13.9 + 13.8	+ 13.8 + 13.7	V Min	
	WW		-13.6	13.4 13.2	-13.4 - 13.2	- 13.3 - 13.2	V Min	
		Supply = $+5V$ (Note 4)	4.0	3.9 3.8	3.9 3.8	3.8 3.7	V Min	
	W	WW.100Y.CO.	1.4	1.6 1.8	1.6 1.8	1.7 1.8	V Max	
CMRR	Common-Mode Rejection Ratio	$-10V \le V_{CM} \le +10V$	102	88 82	88 84	80 78	dB Min	
PSRR	Power Supply Rejection Ratio	$\pm 10V \le V^{\pm} \le \pm 16V$	104	88 82	88 84	80 78	dB Min	
Vo	Output Voltage Swing	Supply = $\pm 15V$, R _L = 2 k Ω	+ 14.2	+ 13.5 + 13.3	+ 13.5 + 13.3	+ 13.4 + 13.3	V Min	
		WW 1005	-13.4	- 13.0 - 12.7	13.0 12.8	- 12.9 - 12.8	V Min	

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WWW.100Y.COM.TW DC Electrical Characteristics (Continued)

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100X.COM.TV

The following specifications apply for Supply Voltage = \pm 15V, V_{CM} = 0, R_L \geq 100 k Ω and R_S = 50 Ω unless otherwise noted. **Boldface** limits apply for $T_A = T_J = T_{MIN}$ to T_{Max} ; all other limits $T_A = T_J = 25^{\circ}C$.

TIM		N 1001. ON		LM6165	LM6265	LM6365	Units
Symbol	Parameter	Conditions	Тур	Limit (Notes 3, 11)	Limit (Note 3)	Limit (Note 3)	
V _O (Continued)	Output Voltage Swing (Continued)	Supply = $+5V$ R _L = 2 k Ω (Note 4)	4.2	3.5 3.3	3.5 3.3	3.4 3.3	V Min
N.COM	TW V	WW.1001.CC	1.3	1.7 2.0	1.7 1.9	1.8 1.9	V Max
	Output Short Circuit Current	Source	65	30 20	30 25	30 25	mA Min
100Y.CO	M.TW	Sink	65	30 20	30 25	30 25	mA Min
ls	Supply Current	WWW.100	5.0	6.5 6.8	6.5 6.7	6.8 6.9	mA Max

AC Electrical Characteristics

The following specifications apply for Supply Voltage = \pm 15V, V_{CM} = 0, R_L \geq 100 k Ω and R_S = 50 Ω unless otherwise noted. **Boldface** limits apply for $T_A = T_J = T_{MIN}$ to T_{MAX} ; all other limits $T_A = T_J = 25^{\circ}C$. (Note 5)

Symbol Param	COM.	WWW N	Тур	LM6165	LM6265	LM6365	Units
	Parameter	Conditions		Limit (Notes 3, 11)	Limit (Note 3)	Limit (Note 3)	
GBW Gain Bandwidth	F = 20 MHz	725	575 350	575	500	MHz	
WW	Product	Supply = ±5V	500	MY.COM	WT	N	Min
SR Slew Rate	A _V = +25 (Note 8)	300	200 180	200	200	V/µs	
	WW.Low CO	Supply = $\pm 5V$	200	.CO	Wn		Min
PBW	Power Bandwidth Product	$V_{OUT} = 20 V_{PP}$	4.5	V.100Y.CC	MI.L		MHz
t _S	Settling Time	10V Step to 0.1% A _V = -25 , R _L = 2 k Ω	80	W.100Y.C	ON.T	N	ns
φ _m	Phase Margin	$A_V = +25$	45	Yooy		1	Deg
A _D	Differential Gain	NTSC, $A_V = +25$	<0.1	WW.IO	COM.	- N	%
φD	Differential Phase	NTSC, $A_V = +25$	<0.1	-100 ·	Mo		Deg
e _{np-p}	Input Noise Voltage	F = 10 kHz	5	100	N.Co	NT.	nV/√Hz
i _{np-p}	Input Noise Current	F = 10 kHz	1.5	WW.L	N.CO	Wa	pA/√Hz

Note 1: Continuous short-circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Note 2: The typical junction-to-ambient thermal resistance of the molded plastic DIP (N) is 105°C/Watt, and the molded plastic SO (M) package is 155°C/Watt, and the cerdip (J) package is 125°C/Watt. All numbers apply for packages soldered directly into a printed circuit board.

Note 3: All limits guaranteed by testing or correlation.

Note 4: For single supply operation, the following conditions apply: V + = 5V, V - = 0V, V_{CM} = 2.5C, V_{OUT} = 2.5V. Pin 1 & Pin 8 (V_{OS} Adjust) are each connected to Pin 4 (V-) to realize maximum output swing. This connection will degrade VOS.

Note 5: $C_1 \leq 5 \text{ pF}$.

Note 6: In order to achieve optimum AC performance, the input stage was designed without protective clamps. Exeeding the maximum differential input voltage results in reverse breakdown of the base-emitter junction of one of the input transistors and probable degradation of the input parameters (especially VOS, IOS, and Noise)

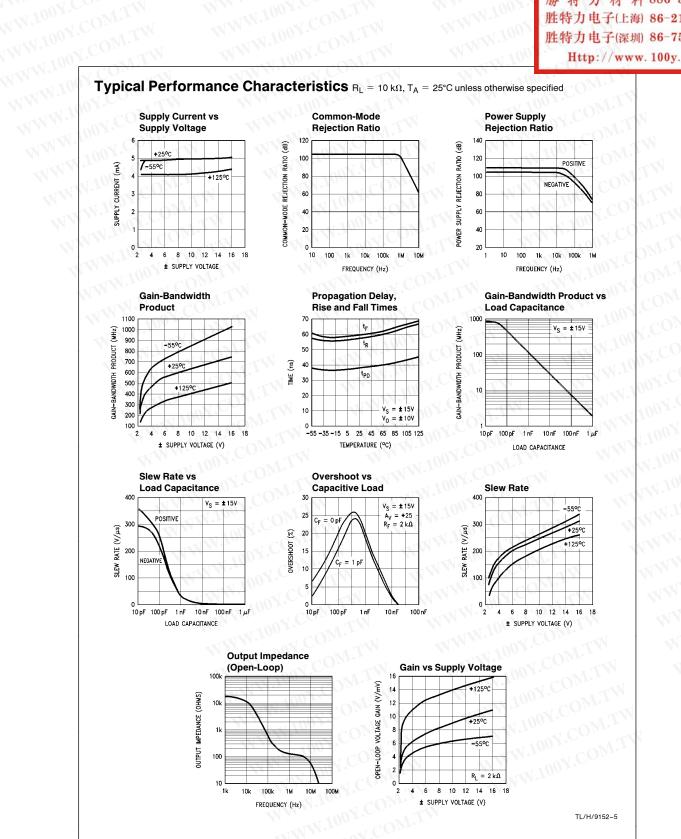
Note 7: The average voltage that the weakest pin combinations (those involving Pin 2 or Pin 3) can withstand and still conform to the datasheet limits. The test circuit used consists of the human body model of 100 pF in series with 1500 $\!\Omega.$

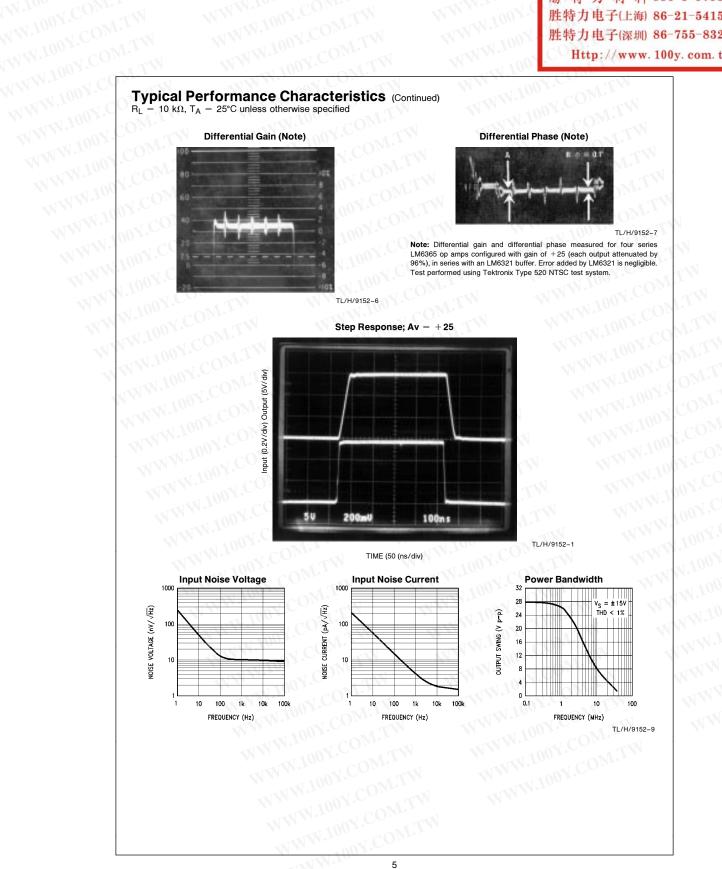
Note 8: $V_{IN} = 0.8V$ step. For supply = $\pm 5V$, $V_{IN} = 0.2V$ step.

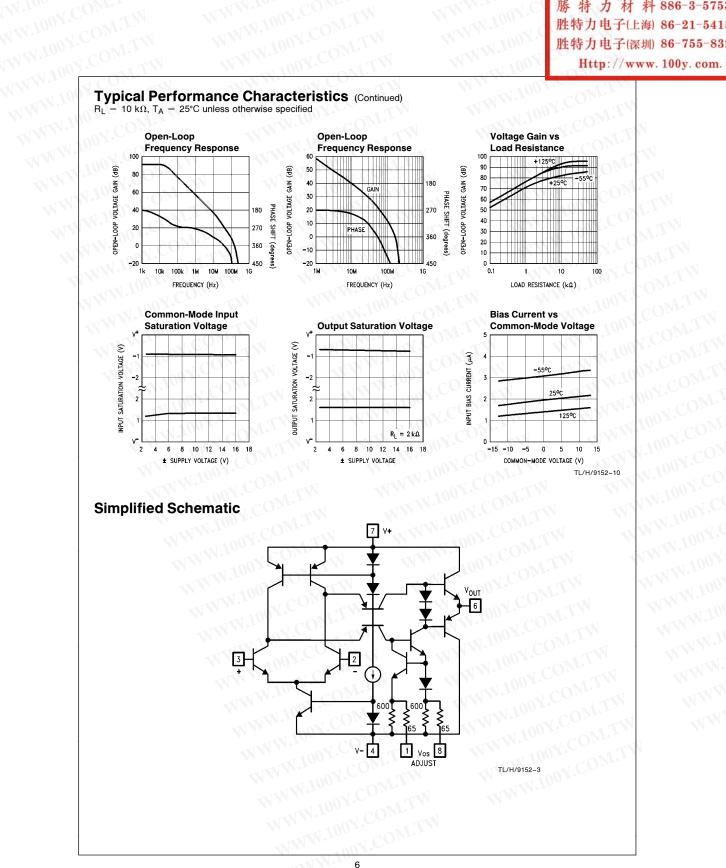
Note 9: Voltage Gain is the total output swing (20V) divided by the input signal required to produce that swing.

Note 10: The voltage between V $^+$ and either input pin must not exceed 36V.

Note 11: A military RETS electrical test specification is available on request. At the time of printing, the LM6165J/883 RETS spec complied with the Boldface limits in this column. The LM6165J/883 may also be procured as Standard Military Drawing #5962-8962501PA.







WWW.100Y.COM.T **Applications Tips**

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The LM6365 is stable for gains of 25 or greater. The LM6361 and LM6364, specified in separate datasheets, are compensated versions of the LM6365. The LM6361 is unitygain stable, while the LM6364 is stable for gains as low as 5. The LM6361, and LM6364 have the same high slew rate as the LM6365, typically 300 V/µs.

To use the LM6365 for gains less than 25, a series resistorcapacitor network should be added between the input pins (as shown in the Typical Applications, Noise Gain Compensation) so that the high-frequency noise gain rises to at least 25.

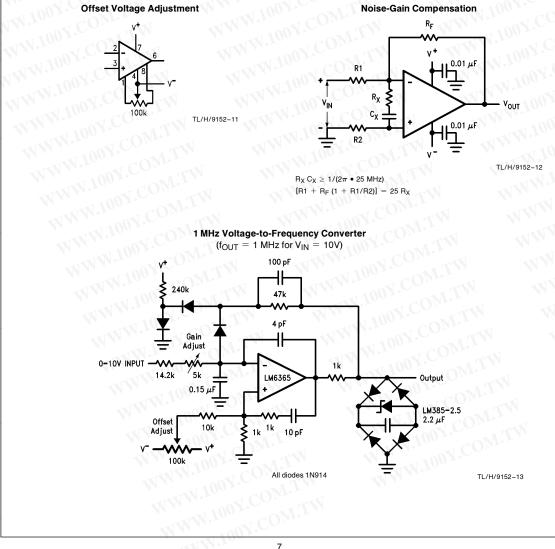
Power supply bypassing will improve stability and transient response of the LM6365, and is recommended for every design. 0.01 µF to 0.1 µF ceramic capacitors should be

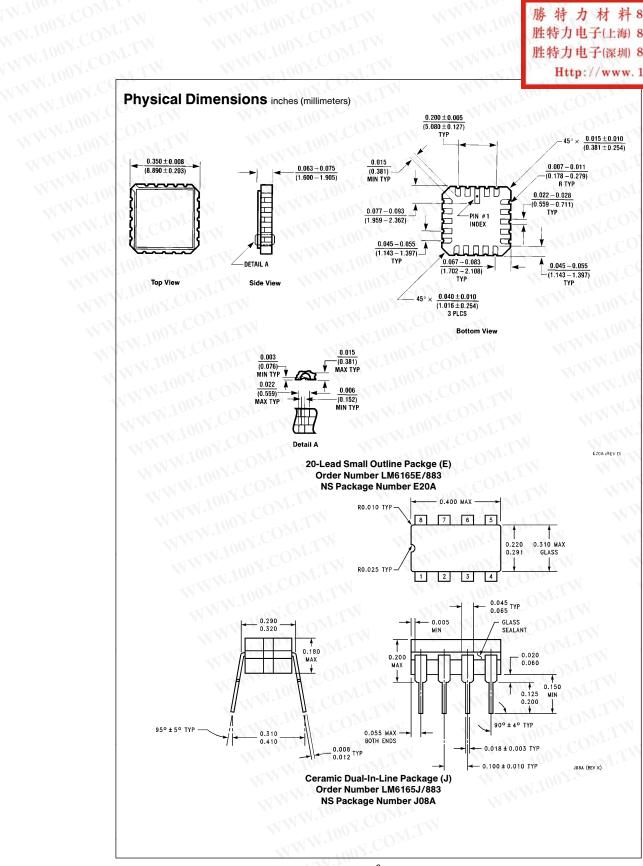
Typical Applications

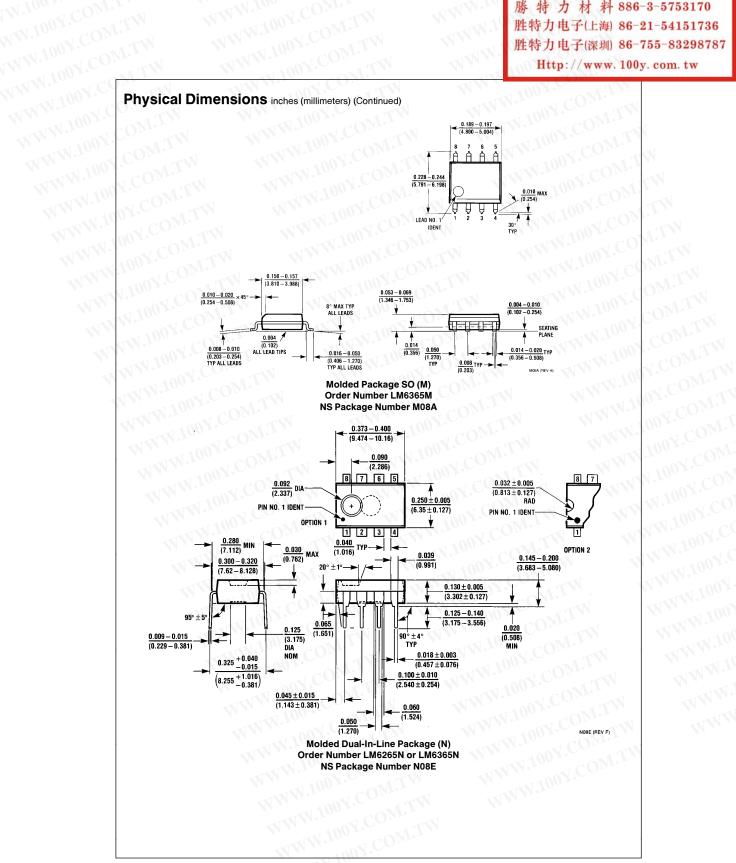
used (from each supply "rail" to ground); an additional 2.2 µF to 10 µF (tantalum) may be required for extra noise reduction.

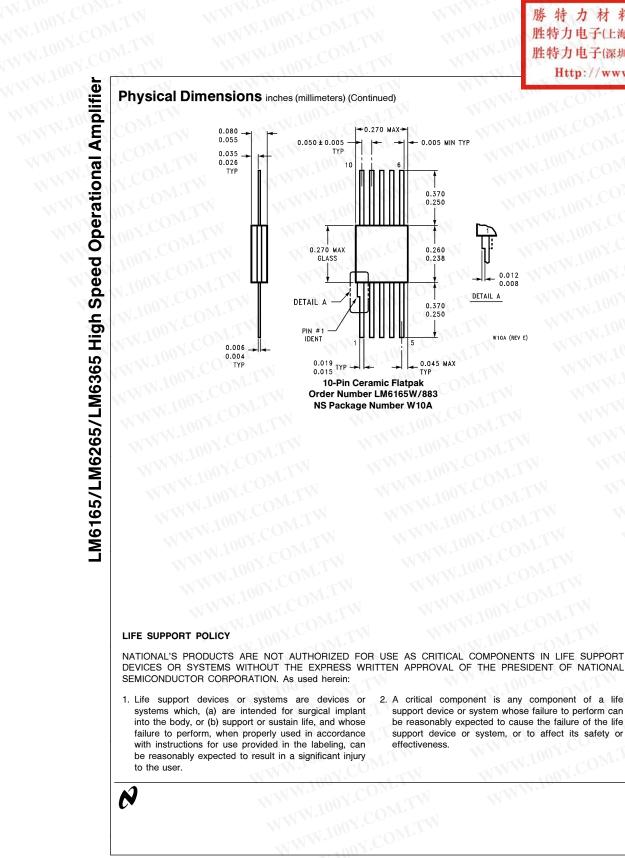
Keep all leads short to reduce stray capacitance and lead inductance, and make sure ground paths are low-impedance, especially where heavier currents will be flowing. Stray capacitance in the circuit layout can cause signal coupling between adjacent nodes, and can cause circuit gain to unintentionally vary with frequency.

Breadboarded circuits will work best if they are built using generic PC boards with a good ground plane. If the op amps are used with sockets, as opposed to being soldered into the circuit, the additional input capacitance may degrade circuit performance.









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